

FEATURES

- 10μs Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated MMC Base with AlN Substrates

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 3300V and currents up to 2400A.

The DIM800FSM12-A000 is a single switch 1200V, n channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus full 10μs short circuit withstand. This module is optimised applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM800FSM12-A000

Note: When ordering, please use the whole part number.

KEY PARAMETERS

| | | |
|-----------------|-------|-------|
| V_{CES} | | 1200V |
| $V_{CE(sat)}$ * | (typ) | 2.2V |
| I_C | (max) | 800A |
| $I_{C(PK)}$ | (max) | 1600A |

*(measured at the power busbars and not the auxiliary terminals)

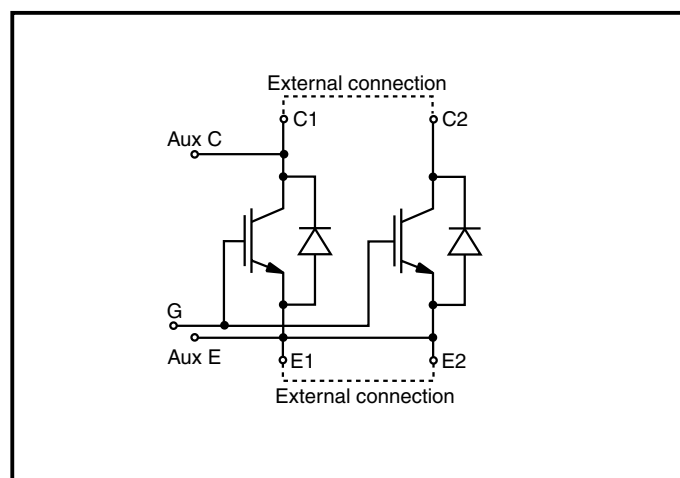


Fig. 1 Single switch circuit diagram

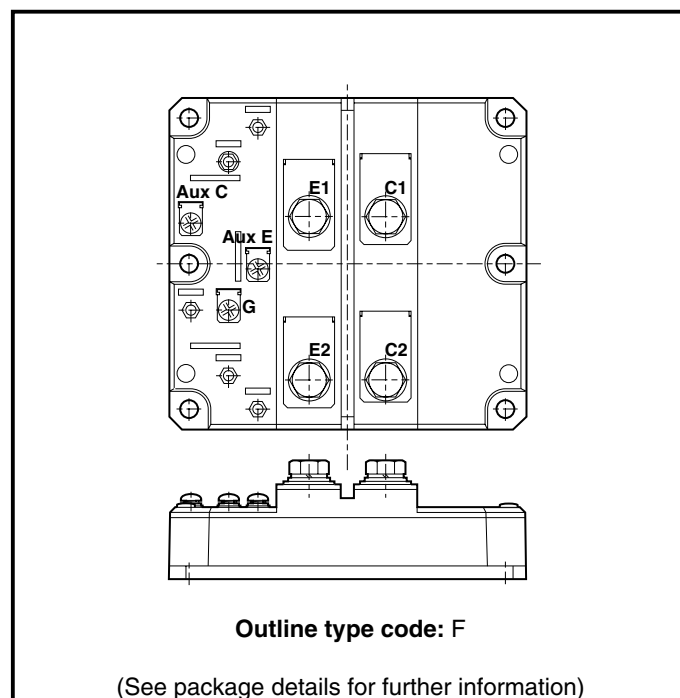


Fig. 2 Electrical connections - (not to scale)

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

| Symbol | Parameter | Test Conditions | Max. | Units |
|-------------|-----------------------------------|------------------------------------------------------------------|----------|-----------------------|
| V_{CES} | Collector-emitter voltage | $V_{GE} = 0\text{V}$ | 1200 | V |
| V_{GES} | Gate-emitter voltage | - | ± 20 | V |
| I_C | Continuous collector current | $T_{case} = 85^{\circ}\text{C}$ | 800 | A |
| $I_{C(PK)}$ | Peak collector current | 1ms, $T_{case} = 115^{\circ}\text{C}$ | 1600 | A |
| P_{max} | Max. transistor power dissipation | $T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$ | 6940 | W |
| I^2t | Diode I^2t value | $V_R = 0$, $t_p = 10\text{ms}$, $T_{vj} = 125^{\circ}\text{C}$ | 100 | kA^2s |
| V_{isol} | Isolation voltage - per module | Commoned terminals to base plate. AC RMS, 1 min, 50Hz | 2500 | V |
| Q_{PD} | Partial discharge - per module | IEC1287. $V_1 = 1300\text{V}$, $V_2 = 1000\text{V}$, 50Hz RMS | 10 | PC |

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AlN
 Baseplate material: AlSiC
 Creepage distance: 20mm
 Clearance: 10mm
 CTI (Critical Tracking Index): 175

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------|-------------------------------------------------------|-----------------------------------------------|------|------|------|-------|
| $R_{th(j-c)}$ | Thermal resistance - transistor | Continuous dissipation - junction to case | - | - | 18 | °C/kW |
| $R_{th(j-c)}$ | Thermal resistance - diode | Continuous dissipation - junction to case | - | - | 40 | °C/kW |
| $R_{th(c-h)}$ | Thermal resistance - case to heatsink (per module) | Mounting torque 5Nm (with mounting grease) | - | - | 8 | °C/kW |
| T_j | Junction temperature | Transistor | - | - | 150 | °C |
| | | Diode | - | - | 125 | °C |
| T_{stg} | Storage temperature range | - | -40 | - | 125 | °C |
| - | Screw torque | Mounting - M6 | - | - | 5 | Nm |
| | | Electrical connections - M4 | - | - | 2 | Nm |
| | | Electrical connections - M8 | - | - | 10 | Nm |

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise.

| Symbol | Parameter | Test Conditions | | Min. | Typ. | Max. | Units |
|-----------------------------------|--------------------------------------|--------------------------------------------------------------------------------------|----------------|------|------|------|-------|
| I _{CES} | Collector cut-off current | V _{GE} = 0V, V _{CE} = V _{CES} | | - | - | 1 | mA |
| | | V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C | | - | - | 25 | mA |
| I _{GES} | Gate leakage current | V _{GE} = ±20V, V _{CE} = 0V | | - | - | 4 | μA |
| V _{GE(TH)} | Gate threshold voltage | I _C = 40mA, V _{GE} = V _{CE} | | 4.5 | 5.5 | 6.5 | V |
| V _{CE(sat)} [†] | Collector-emitter saturation voltage | V _{GE} = 15V, I _C = 800A | | - | 2.2 | 2.8 | V |
| | | V _{GE} = 15V, I _C = 800A, , T _{case} = 125°C | | - | 2.6 | 3.2 | V |
| I _F | Diode forward current | DC | | - | - | 800 | A |
| I _{FM} | Diode maximum forward current | t _p = 1ms | | - | - | 1600 | A |
| V _F [†] | Diode forward voltage | I _F = 800A | | - | 2.1 | 2.4 | V |
| | | I _F = 800A, T _{case} = 125°C | | - | 2.1 | 2.4 | V |
| C _{ies} | Input capacitance | V _{CE} = 25V, V _{GE} = 0V, f = 1MHz | | - | 90 | - | nF |
| L _M | Module inductance | - | | - | 20 | - | nH |
| R _{INT} | Internal transistor resistance | - | | - | 0.27 | - | mΩ |
| SC _{Data} | Short circuit. I _{SC} | T _j = 125°C, V _{CC} = 900V, | I ₁ | - | 5500 | - | A |
| | | t _p ≤ 10μs, V _{CE(max)} = V _{CES} - L*. di/dt | I ₂ | - | 4500 | - | A |
| | | IEC 60747-9 | | | | | |

Note:

\dagger Measured at the power busbars and not the auxiliary terminals)

L^* is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------------|-------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $t_{d(off)}$ | Turn-off delay time | $I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = R_{G(OFF)} = 2.7\Omega$ $L \sim 100\text{nH}$ | - | 1250 | - | ns |
| t_f | Fall time | | - | 170 | - | ns |
| E_{OFF} | Turn-off energy loss | | - | 130 | - | mJ |
| $t_{d(on)}$ | Turn-on delay time | | - | 250 | - | ns |
| t_r | Rise time | | - | 250 | - | ns |
| E_{ON} | Turn-on energy loss | | - | 80 | - | mJ |
| Q_g | Gate charge | | - | 9.0 | - | μC |
| Q_{rr} | Diode reverse recovery charge | $I_F = 800\text{A}, V_R = 600\text{V},$ $di_F/dt = 4200\text{A}/\mu\text{s}$ | - | 80 | - | μC |
| I_{rr} | Diode reverse current | | - | 380 | - | A |
| E_{REC} | Diode reverse recovery energy | | - | 30 | - | mJ |

$T_{case} = 125^{\circ}\text{C}$ unless stated otherwise

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------------|-------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $t_{d(off)}$ | Turn-off delay time | $I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = R_{G(OFF)} = 2.7\Omega$ $L \sim 100\text{nH}$ | - | 1500 | - | ns |
| t_f | Fall time | | - | 200 | - | ns |
| E_{OFF} | Turn-off energy loss | | - | 160 | - | mJ |
| $t_{d(on)}$ | Turn-on delay time | | - | 400 | - | ns |
| t_r | Rise time | | - | 220 | - | ns |
| E_{ON} | Turn-on energy loss | | - | 120 | - | mJ |
| Q_{rr} | Diode reverse recovery charge | $I_F = 800\text{A}, V_R = 600\text{V},$ $di_F/dt = 4000\text{A}/\mu\text{s}$ | - | 160 | - | μC |
| I_{rr} | Diode reverse current | | - | 450 | - | A |
| E_{REC} | Diode reverse recovery energy | | - | 60 | - | mJ |

TYPICAL CHARACTERISTICS

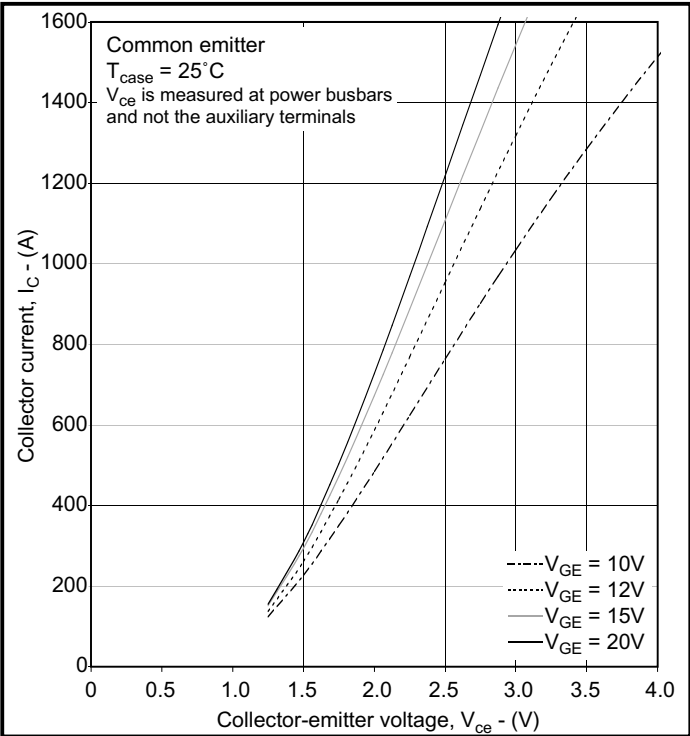


Fig. 3 Typical output characteristics

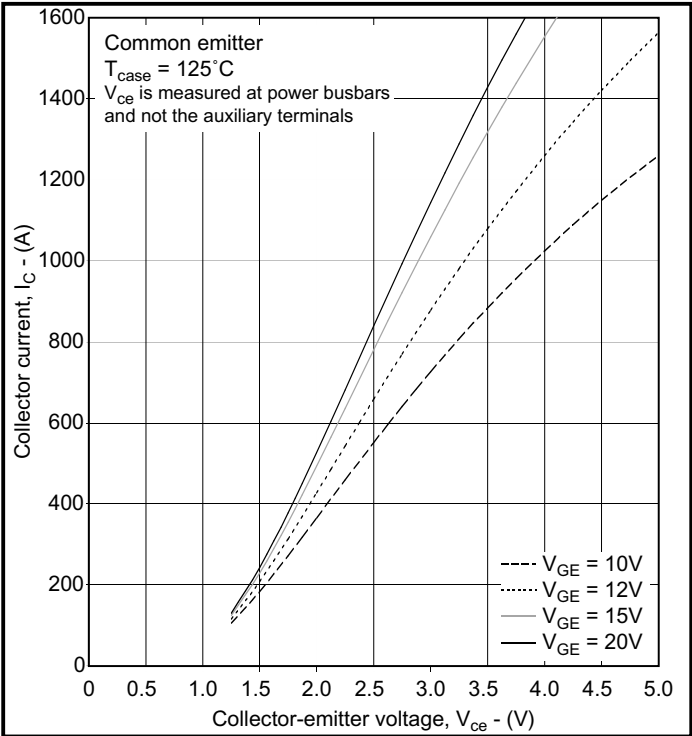


Fig. 4 Typical output characteristics

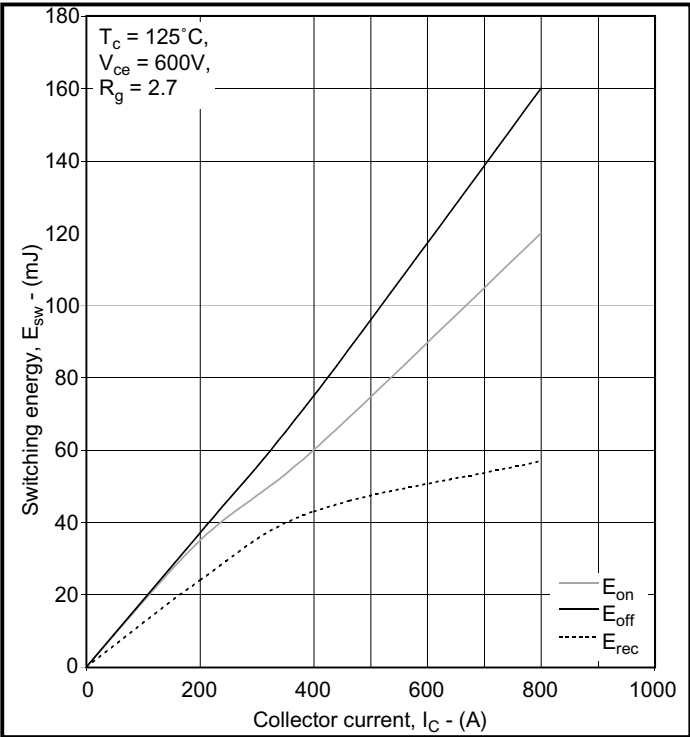


Fig. 5 Typical switching energy vs collector current

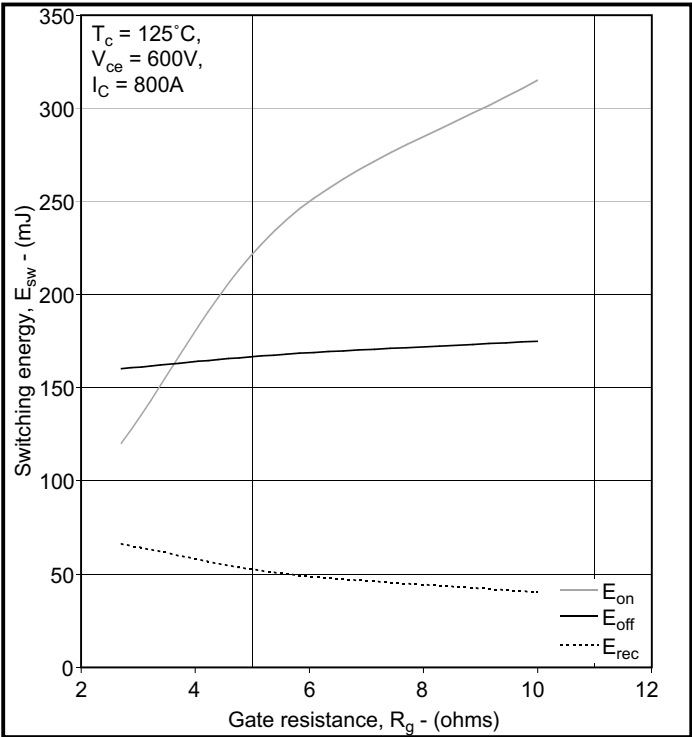


Fig. 6 Typical switching energy vs gate resistance

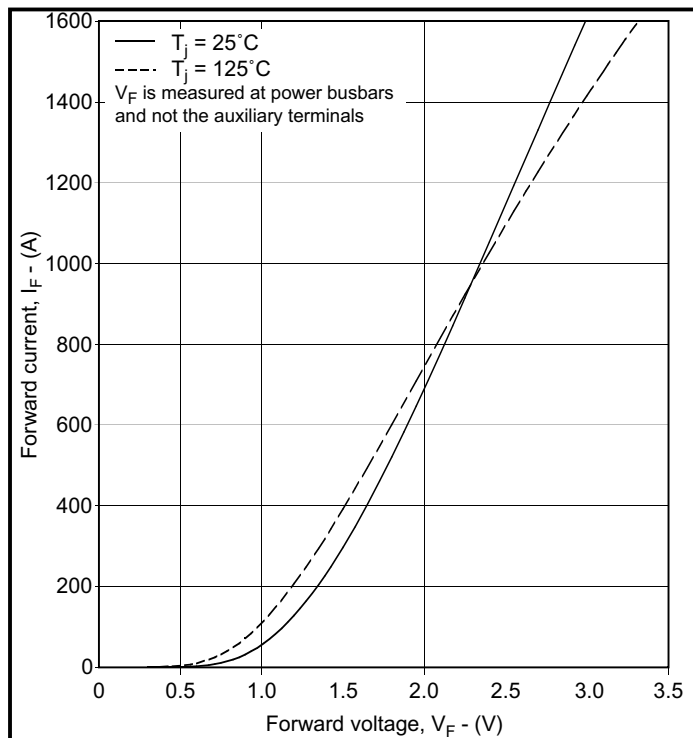


Fig. 7 Diode typical forward characteristics

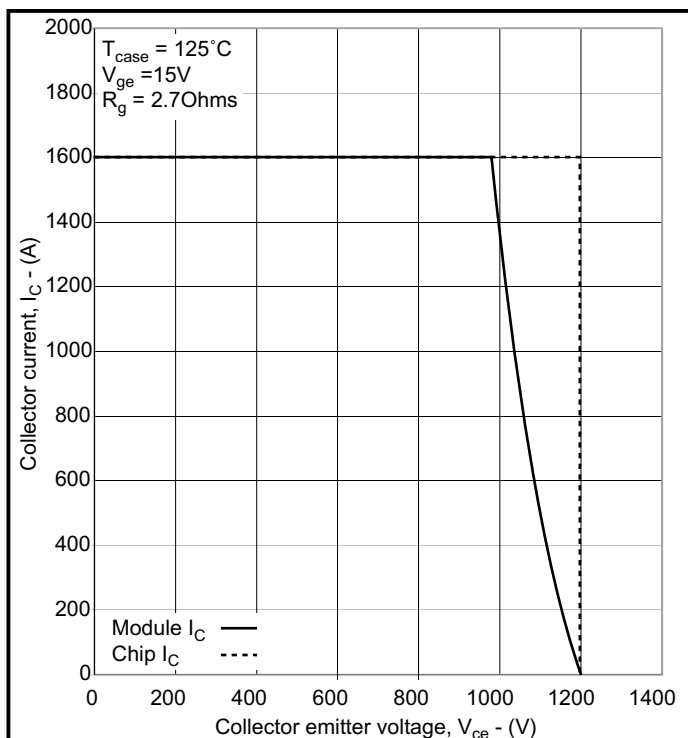


Fig. 8 Reverse bias safe operating area

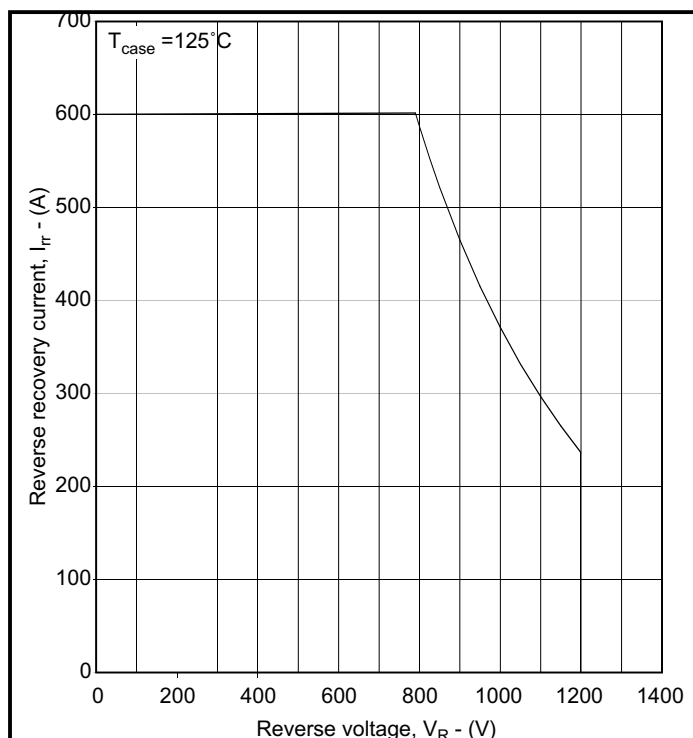


Fig. 9 Diode reverse bias safe operating area

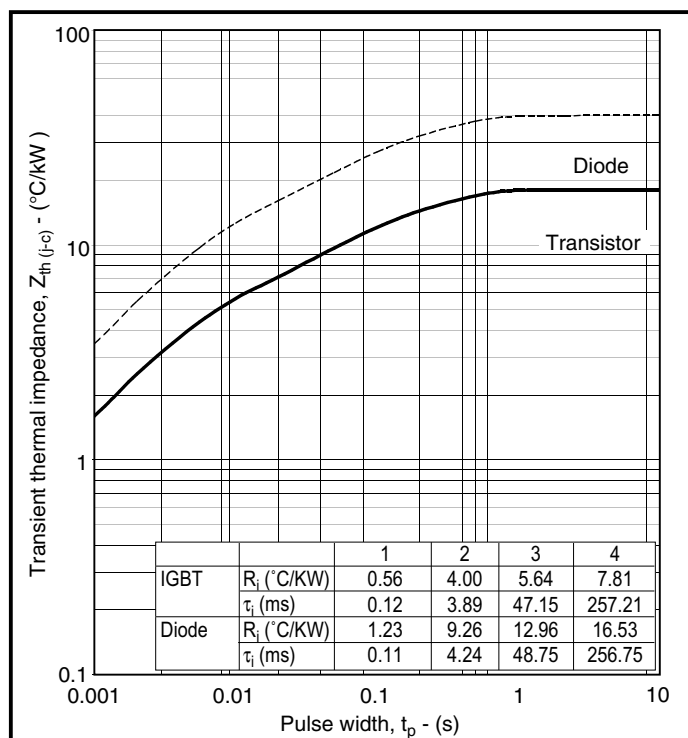


Fig. 10 Transient thermal impedance

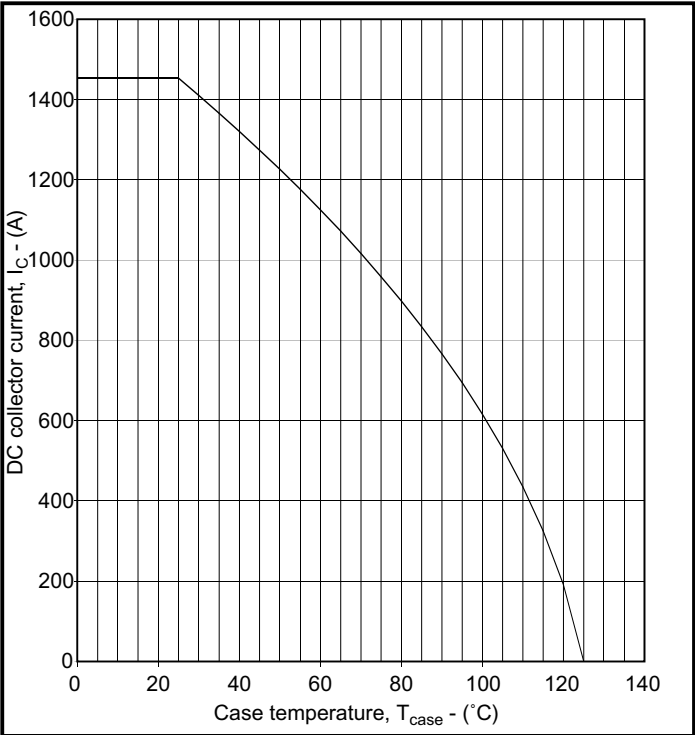
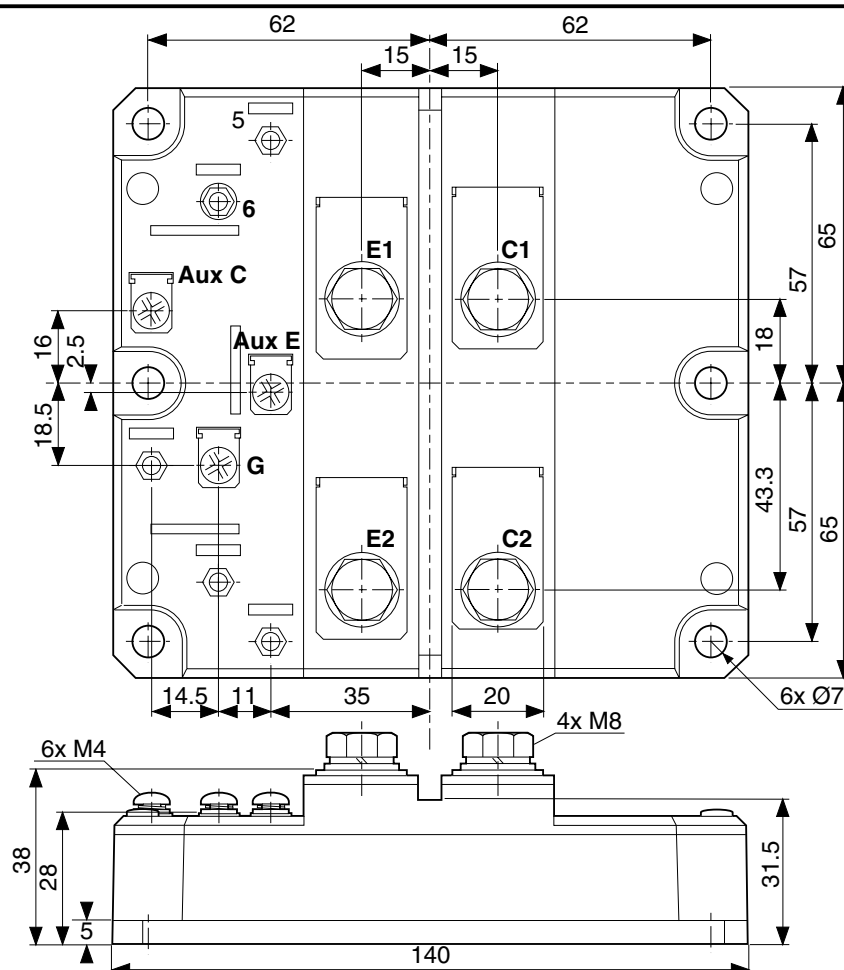


Fig. 12 DC current rating vs case temperature

PACKAGE DETAILS

For further package information please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Main Terminal screw plastic hole depth (M8) = 16.8 ± 0.3

Auxiliary and Gate pin plastic hole depth (M4) = 9 ± 0.3

Copper terminal thickness, Main Terminal pins = 1.5 ± 0.1

Copper terminal thickness, Auxiliary and Gate pin = 0.9 ± 0.1

Nominal weight: 1050g

Module outline type code: F

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

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No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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